

Emitter common (dual digital transistors)

EMA11 / UMA11N / FMA11A

●Features

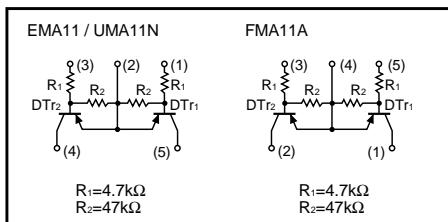
- 1) Two DTA143Z chips in a EMT or UMT or SMT package.
- 2) Mounting cost and area can be cut in half.

●Structure

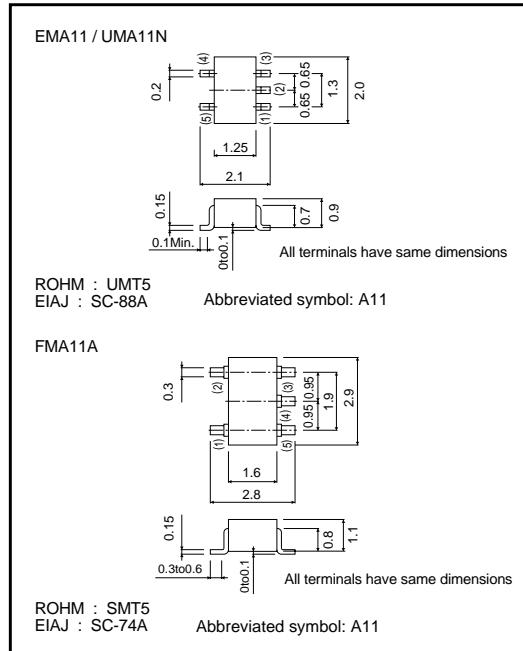
Epitaxial planar type
PNP silicon transistor
(Built-in resistor type)

The following characteristics apply to both DTr₁ and DTr₂.

●Equivalent circuit



●External dimensions (Units : mm)



●Packaging specifications

Type	Package		Taping		
	Code	T2R	TR	T148	
		Basic ordering unit (pieces)	8000	3000	3000
EMA11		○	—	—	
UMA11N		—	○	—	
FMA11A		—	—	○	

●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{cc}	-50	V
Input voltage	V _{IN}	-30 5	V
Output current	I _o I _c (Max.)	-100 -100	mA
Power dissipation	EMA11 / UMA11N FMA11A	P _d 150 (TOTAL) 300 (TOTAL)	mW *1 *2
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

*1 120mW per element must not be exceeded.

*2 200mW per element must not be exceeded.

Transistors

● Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{I(\text{off})}$	—	—	-0.5	V	$V_{CC}=-5\text{V}, I_O=-100\mu\text{A}$
	$V_{I(\text{on})}$	-1.3	—	—		$V_O=-0.3\text{V}, I_O=5\text{mA}$
Output voltage	$V_O(\text{on})$	—	-0.1	-0.3	V	$I_O/I_I=-5\text{mA}/-0.25\text{mA}$
Input current	I_I	—	—	-1.8	mA	$V_I=-5\text{V}$
Output current	$I_O(\text{off})$	—	—	-0.5	μA	$V_{CC}=-50\text{V}, V_I=0\text{V}$
DC current gain	G_I	80	—	—	—	$V_O=-5\text{V}, I_O=-10\text{mA}$
Transition frequency	f_T	—	250	—	MHz	$V_{CE}=10\text{mA}, I_E=5\text{mA}, f=100\text{MHz}$ *
Input resistance	R_I	3.29	4.7	6.11	kΩ	—
Resistance ratio	R_2/R_1	8	10	12	—	—

* Transition frequency of the device

● Electrical characteristic curves

